

# Paul Fons

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6137797/publications.pdf>

Version: 2024-02-01

341  
papers

10,732  
citations

31949

53  
h-index

43868

91  
g-index

348  
all docs

348  
docs citations

348  
times ranked

7099  
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoinduced Tellurium Segregation in MoTe <sub>2</sub> . Physica Status Solidi - Rapid Research Letters, 2022, 16, .	1.2	10
2	The formation of a one-dimensional van der Waals selenium crystal from the three-dimensional amorphous phase: A spectroscopic signature of van der Waals bonding. Applied Physics Letters, 2022, 120, 033103.	1.5	2
3	Improved Ordering of Quasi-Two-Dimensional MoS <sub>2</sub> via an Amorphous-to-Crystal Transition Initiated from Amorphous Sulfur-Rich MoS <sub>2+x</sub> . Crystal Growth and Design, 2022, 22, 3072-3079.	1.4	7
4	Phase control of sputter-grown large-area MoTe <sub>2</sub> films by preferential sublimation of Te: amorphous, 1T and 2H phases. Journal of Materials Chemistry C, 2022, 10, 10627-10635.	2.7	9
5	Electric Fields and Interfacial Phase-Change Memory Structures. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000412.	1.2	3
6	Chalcogenide Materials Engineering for Phase-Change Memory and Future Electronics Applications: From Sb <sub>2</sub> Te to Bi <sub>2</sub> Te. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000414.	1.2	7
7	Phase Change Materials for Optical Disc and Display Applications. , 2021, , 681-711.		0
8	Ultrafast scattering dynamics of coherent phonons in Bi <sub>1-x</sub> Sb <sub>x</sub> in the Weyl semimetal phase. New Journal of Physics, 2021, 23, 023034.	1.2	2
9	Dimensional transformation of chemical bonding during crystallization in a layered chalcogenide material. Scientific Reports, 2021, 11, 4782.	1.6	16
10	Dielectric relaxation in amorphous and crystalline Sb <sub>2</sub> Te <sub>3</sub> thin films. Journal of Materials Science: Materials in Electronics, 2021, 32, 14072-14078.	1.1	5
11	Role of the Cu <sub>2</sub> -Deficient Interface in Cu <sub>2</sub> Te <sub>3</sub> Phase-Change Material. Applied Surface Science, 2021, 516, 147314.	1.5	13
12	Understanding the low resistivity of the amorphous phase of Cu <sub>2</sub> Te <sub>3</sub> phase-change material: Experimental evidence for the key role of Cr clusters. Physical Review Materials, 2021, 5, .	0.9	4
13	Evolution of the local structure surrounding nitrogen atoms upon the amorphous to crystalline phase transition in nitrogen-doped Cr <sub>2</sub> Ge <sub>2</sub> Te <sub>6</sub> phase-change material. Applied Surface Science, 2021, 556, 149760.	3.1	4
14	Crystallization of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> under high hydrostatic pressures: Differences in nanoscale atomic ordering in as-deposited and pressure-induced amorphous phases. Journal of Alloys and Compounds, 2021, 874, 159980.	2.8	3
15	Polymorphism of CdTe in the Few-Monolayer Limit. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100358.	1.2	3
16	Amorphous-to-Crystal Transition in Quasi-Two-Dimensional MoS <sub>2</sub> : Implications for 2D Electronic Devices. ACS Applied Nano Materials, 2021, 4, 8834-8844.	2.4	22
17	Recent developments concerning the sputter growth of chalcogenide-based layered phase-change materials. Materials Science in Semiconductor Processing, 2021, 135, 106079.	1.9	12
18	Phase-Change Alloys: Structural Aspects. , 2021, , 323-339.		0

#	ARTICLE	IF	CITATIONS
19	Crystalline Sb <sub>2</sub> Te <sub>3</sub> : Side Surfaces and Disappearance of Dirac Cones. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000418.	1.2	2
20	Polycrystalline CuGaSe <sub>2</sub> thin film growth and photovoltaic devices fabricated on alkali-free and alkali-containing substrates. Journal of Crystal Growth, 2020, 532, 125407.	0.7	5
21	Dielectric Relaxation and Charge Transfer in Amorphous MoS <sub>2</sub> Thin Films. Physica Status Solidi (B): Basic Research, 2020, 257, 2000114.	0.7	5
22	The importance of contacts in Cu <sub>2</sub> GeTe <sub>3</sub> phase change memory devices. Journal of Applied Physics, 2020, 128, .	1.1	11
23	Effects of electric and magnetic fields on the resistive switching operation of iPCM. Applied Physics Letters, 2020, 116, 201903.	1.5	1
24	Lithium-Doping Effects in Cu(In,Ga)Se <sub>2</sub> Thin-Film and Photovoltaic Properties. ACS Applied Materials & Interfaces, 2020, 12, 25058-25065.	4.0	14
25	Polarization Processes in Thin Layers of Amorphous MoS <sub>2</sub> Obtained by RF Magnetron Sputtering. Semiconductors, 2020, 54, 558-562.	0.2	0
26	Structural Metastability in Chalcogenide Semiconductors: The Role of Chemical Bonding. Physica Status Solidi (B): Basic Research, 2020, 257, 2000138.	0.7	3
27	Structural and Dielectric Study of Thin Amorphous Layers of the GeSbTe System Prepared by RF Magnetron Sputtering. Semiconductors, 2020, 54, 201-204.	0.2	0
28	Ultrafast dynamics of the low frequency shear phonon in 1Tâ€²-MoTe <sub>2</sub> . Applied Physics Letters, 2020, 116, .	1.5	21
29	High-quality sputter-grown layered chalcogenide films for phase change memory applications and beyond. Journal Physics D: Applied Physics, 2020, 53, 284002.	1.3	23
30	Soft X-ray Absorption Spectroscopy Probes OH-Interactions in Epoxy-Based Polymers. Journal of Physical Chemistry C, 2020, 124, 9622-9627.	1.5	9
31	Dielectric relaxation in the GeSb <sub>2</sub> Te <sub>4</sub> phase-change material. AIP Conference Proceedings, 2020, , .	0.3	1
32	Dielectric Relaxation and Photo-electromotive Force in Ge-Sb-Te/Si Structures. , 2020, , .		0
33	Photon energy dependence of Kerr rotation in GeTe/Sb <sub>2</sub> Te <sub>3</sub> chalcogenide superlattices. Journal of Physics Condensed Matter, 2019, 31, 415502.	0.7	2
34	Similarities and Critical Differences in Heavy Alkali-Metal Rubidium and Cesium Effects on Chalcopyrite Cu(In,Ga)Se <sub>2</sub> Thin-Film Solar Cells. Journal of Physical Chemistry C, 2019, 123, 17757-17764.	1.5	39
35	Cr-Triggered Local Structural Change in Cr <sub>2</sub> Ge <sub>2</sub> Te <sub>6</sub> Phase Change Material. ACS Applied Materials & Interfaces, 2019, 11, 43320-43329.	4.0	26
36	Switching of the Optical Properties of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> Phase Change Material in the Terahertz Frequency Region. , 2019, , .		0

#	ARTICLE	IF	CITATIONS
37	Terahertz spectroscopic characterization of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> phase change materials for photonics applications. Journal of Materials Chemistry C, 2019, 7, 8209-8215.	2.7	38
38	Transient Fano Resonance in topological insulators observed by coherent phonon spectroscopy. EPJ Web of Conferences, 2019, 205, 04021.	0.1	0
39	High-Speed Bipolar Switching of Sputtered GeTe/SbTe Superlattice iPCM with Enhanced Cyclability. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900105.	1.2	14
40	Systematic materials design for phase-change memory with small density changes for high-endurance non-volatile memory applications. Applied Physics Express, 2019, 12, 051008.	1.1	7
41	Chalcogenide van der Waals superlattices: a case example of interfacial phase-change memory. Pure and Applied Chemistry, 2019, 91, 1777-1786.	0.9	5
42	Origin of resistivity contrast in interfacial phase-change memory: The crucial role of Ge/Sb intermixing. Applied Physics Letters, 2019, 114, .	1.5	37
43	Investigation of the oxidation process in GeTe-based phase change alloy using Ge K-edge XANES spectroscopy. Pure and Applied Chemistry, 2019, 91, 1769-1775.	0.9	2
44	Terahertz generation measurements of multilayered GeTe/Sb <sub>2</sub> Te <sub>3</sub> phase change materials. Optics Letters, 2019, 44, 1355.	1.7	8
45	Resistive switching characteristics of interfacial phase-change memory at elevated temperature. Japanese Journal of Applied Physics, 2018, 57, 04FE06.	0.8	7
46	Coherent Dirac plasmons in topological insulators. Physical Review B, 2018, 97, .	1.1	11
47	Si-doped Cu(In,Ga)Se <sub>2</sub> Photovoltaic Devices with Energy Conversion Efficiencies Exceeding 16.5% without a Buffer Layer. Advanced Energy Materials, 2018, 8, 1702391.	10.2	8
48	Understanding the fast phase-change mechanism of tetrahedrally bonded $\text{Cu}_2\text{Te}$ : Comprehensive analyses of electronic structure and transport phenomena. Physical Review B, 2018, 97, .	1.1	11
49	A cascading nonlinear magneto-optical effect in topological insulators. Scientific Reports, 2018, 8, 3908.	1.6	10
50	(Invited) Sputter Growth of Chalcogenide Superlattice Films for Future Phase Change Memory Applications. ECS Transactions, 2018, 86, 49-54.	0.3	5
51	Zener Tunneling Breakdown in Phase-Change Materials Revealed by Intense Terahertz Pulses. Physical Review Letters, 2018, 121, 165702.	2.9	17
52	Reconfiguration of van der Waals Gaps as the Key to Switching in GeTe/Sb <sub>2</sub> Te <sub>3</sub> Superlattices. MRS Advances, 2018, 3, 3413-3418.	0.5	2
53	Optical Detection of Periodic Structure of Chalcogenide Superlattice Using Coherent Folded Acoustic Phonons. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800246.	1.2	0
54	Topological Phase Buried in a Chalcogenide Superlattice Monitored by Helicity-Dependent Kerr Measurement. ACS Applied Materials & Interfaces, 2018, 10, 26781-26786.	4.0	4

#	ARTICLE	IF	CITATIONS
55	Effects of RbF postdeposition treatment and heat-light soaking on the metastable acceptor activation of CuInSe <sub>2</sub> thin film photovoltaic devices. Applied Physics Letters, 2018, 113, .	1.5	25
56	Detection of N-Te bonds in the as-deposited amorphous nitrogen-doped GeTe-based phase change alloys using N K-edge XANES spectroscopy and their impact on crystallization. Journal of Alloys and Compounds, 2017, 704, 254-259.	2.8	5
57	Atomic Reconfiguration of van der Waals Gaps as the Key to Switching in GeTe/Sb <sub>2</sub> Te <sub>3</sub> Superlattices. ACS Omega, 2017, 2, 6223-6232.	1.6	58
58	Enhancement of coherent phonon amplitude in phase-change materials by near-infrared laser irradiation. Applied Physics Letters, 2017, 111, .	1.5	4
59	Compositional tuning in sputter-grown highly-oriented BiTe films and their optical and electronic structures. Nanoscale, 2017, 9, 15115-15121.	2.8	19
60	Si-Doping Effects in Cu(In,Ga)Se <sub>2</sub> Thin Films and Applications for Simplified Structure High-Efficiency Solar Cells. ACS Applied Materials & Interfaces, 2017, 9, 31119-31128.	4.0	11
61	A Magnetoresistance Induced by a Nonzero Berry Phase in GeTe/Sb <sub>2</sub> Te <sub>3</sub> Chalcogenide Superlattices. Advanced Functional Materials, 2017, 27, 1702243.	7.8	24
62	Electronic Structure of Transition-Metal Based Cu <sub>2</sub> GeTe <sub>3</sub> Phase Change Material: Revealing the Key Role of Cu <i>d</i> Electrons. Chemistry of Materials, 2017, 29, 7440-7449.	3.2	24
63	Local structure of the crystalline and amorphous states of $\text{Cu}_2\text{GeTe}_3$ alloy without resonant bonding: A combined x-ray absorption and <i>ab initio</i> study. Physical Review B, 2017, 95, .	1.1	14
64	Pressure-Induced Phase Transitions in GeTe-Rich Ge <sub>1-x</sub> Sb <sub>x</sub> Te Alloys across the Rhombohedral-to-Cubic Transitions. Inorganic Chemistry, 2017, 56, 7687-7693.	1.9	3
65	Manipulating the Bulk Band Structure of Artificially Constructed van der Waals Chalcogenide Heterostructures. ACS Applied Materials & Interfaces, 2017, 9, 23918-23925.	4.0	17
66	A comparative study of the effects of sputtering deposition conditions for ZnO surface electrode layers on Cu(In,Ga)Se <sub>2</sub> and CuGaSe <sub>2</sub> solar cells. Thin Solid Films, 2017, 633, 49-54.	0.8	5
67	Phase-Change Memory Materials. Springer Handbooks, 2017, , 1-1.	0.3	4
68	Insights into the physics and chemistry of chalcogenides obtained from x-ray absorption spectroscopy. Semiconductor Science and Technology, 2017, 32, 123003.	1.0	10
69	Strain engineering of atomic and electronic structures of few-monolayer-thick GaN. Physical Review Materials, 2017, 1, .	0.9	18
70	Instability and Spontaneous Reconstruction of Few-Monolayer Thick GaN Graphitic Structures. Nano Letters, 2016, 16, 4849-4856.	4.5	51
71	Interface oxygen and heat sensitivity of Cu(In,Ga)Se <sub>2</sub> and CuGaSe <sub>2</sub> solar cells. Applied Physics Letters, 2016, 108, 203902.	1.5	10
72	A two-step process for growth of highly oriented Sb <sub>2</sub> Te <sub>3</sub> using sputtering. AIP Advances, 2016, 6, .	0.6	47

#	ARTICLE	IF	CITATIONS
73	Electronic excitation-induced semiconductor-to-metal transition in monolayer $\text{MoTe}_2$ . Physical Review B, 2016, 94, .		
74	Enhanced $\text{Sb}_2\text{S}_3$ crystallisation by electric field induced silver doping. Thin Solid Films, 2016, 616, 80-85.	0.8	13
75	Anisotropic lattice response induced by a linearly-polarized femtosecond optical pulse excitation in interfacial phase change memory material. Scientific Reports, 2016, 6, 19758.	1.6	9
76	Sub-nanometre resolution of atomic motion during electronic excitation in phase-change materials. Scientific Reports, 2016, 6, 20633.	1.6	29
77	Self-organized van der Waals epitaxy of layered chalcogenide structures. Physica Status Solidi (B): Basic Research, 2015, 252, 2151-2158.	0.7	61
78	Understanding Phase-Change Memory Alloys from a Chemical Perspective. Scientific Reports, 2015, 5, 13698.	1.6	47
79	Anomalous Phase Change in $[(\text{GeTe})_2/(\text{Sb}_2\text{Te}_3)]_{20}$ Superlattice Observed by Coherent Phonon Spectroscopy. Springer Proceedings in Physics, 2015, , 199-201.	0.1	2
80	Coherent gigahertz phonons in $\text{Ge}_2\text{Sb}_2\text{Te}_5$ phase-change materials. Journal of Physics Condensed Matter, 2015, 27, 485402.	0.7	1
81	Giant multiferroic effects in topological $\text{GeTe-Sb}_2\text{Te}_3$ superlattices. Science and Technology of Advanced Materials, 2015, 16, 014402.	2.8	73
82	Laser-driven switching dynamics in phase change materials investigated by time-resolved X-ray absorption spectroscopy. Phase Transitions, 2015, 88, 82-89.	0.6	3
83	Femtosecond structural transformation of phase-change materials far from equilibrium monitored by coherent phonons. Nature Communications, 2015, 6, 8367.	5.8	62
84	Local structure of epitaxial $\text{GeTe}$ and $\text{Ge}_2\text{Sb}_2\text{Te}_5$ films grown on $\text{InAs}$ and $\text{Si}$ substrates with (100) and (111) orientations: An x-ray absorption near-edge structure study. Journal of Applied Physics, 2015, 117, 125308.	1.1	9
85	Anomalous phase change process in $[(\text{GeTe})_2/(\text{Sb}_2\text{Te}_3)]_{20}$ superlattice observed by coherent phonon spectroscopy. , 2014, , .		0
86	Coherent phonon study of $(\text{GeTe})_m(\text{Sb}_2\text{Te}_3)_n$ interfacial phase change memory materials. Applied Physics Letters, 2014, 105, 151902.	1.5	14
87	Hard x-ray photoelectron spectroscopy study of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ ; as-deposited amorphous, crystalline, and laser-reamorphized. Applied Physics Letters, 2014, 104, 061909.	1.5	7
88	Ge L3-edge x-ray absorption near-edge structure study of structural changes accompanying conductivity drift in the amorphous phase of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ . Journal of Applied Physics, 2014, 115, .	1.1	34
89	Picosecond strain dynamics in $\text{Ge}_2\text{Sb}_2\text{Te}_5$ by time-resolved x-ray diffraction. Physical Review B, 2014, 90, .		
90	Ab-initio calculations and structural studies of $(\text{SiTe})_2(\text{Sb}_2\text{Te}_3)_n$ ( $n : 1, 2, 4$ and $6$ ) phase-change superlattice films. Physica Status Solidi - Rapid Research Letters, 2014, 8, 302-306.	1.2	29

#	ARTICLE	IF	CITATIONS
91	Athermal amorphization of crystallized chalcogenide glasses and phase-change alloys. Physica Status Solidi (B): Basic Research, 2014, 251, 1297-1308.	0.7	15
92	Ferroelectric Order Control of the Dirac Semimetal Phase in $\text{GeTe}_{1-x}\text{Sb}_x$ Superlattices. Advanced Materials Interfaces, 2014, 1, 1300027.	1.9	155
93	Structural tuning of wide-gap chalcopyrite $\text{CuGaSe}_2$ thin films and highly efficient solar cells: differences from narrow-gap $\text{Cu}(\text{In,Ga})\text{Se}_2$ . Progress in Photovoltaics: Research and Applications, 2014, 22, 821-829.	4.4	61
94	Doping of ZnO nanowires using phosphorus diffusion from a spin-on doped glass source. Journal of Applied Physics, 2014, 115, 194302.	1.1	2
95	Buried $p-n$ junction formation in $\text{CuGaSe}_2$ thin-film solar cells. Applied Physics Letters, 2014, 104, 031606.	1.5	27
96	Study of band inversion in the $\text{Pb}_{1-x}\text{Sn}_x\text{Te}$ class of topological crystalline insulators using x-ray absorption spectroscopy. Journal of Physics Condensed Matter, 2014, 26, 475502.	0.7	11
97	Ferroelectric switching in epitaxial GeTe films. APL Materials, 2014, 2, .	2.2	67
98	Excitation-Assisted Disordering of GeTe and Related Solids with Resonant Bonding. Journal of Physical Chemistry C, 2014, 118, 10248-10253.	1.5	27
99	Local structure of the SnTe topological crystalline insulator: Rhombohedral distortions emerging from the rocksalt phase. Physical Review B, 2014, 90, .	1.1	21
100	Interfacial Alkali Diffusion Control in Chalcopyrite Thin-Film Solar Cells. ACS Applied Materials & Interfaces, 2014, 6, 14123-14130.	4.0	23
101	Mirror-symmetric Magneto-optical Kerr Rotation using Visible Light in $[(\text{GeTe})_2(\text{Sb}_2\text{Te}_3)]_n$ Topological Superlattices. Scientific Reports, 2014, 4, 5727.	1.6	57
102	Ultrafast Lattice Dynamics of Phase-change Materials Monitored by a Pump-pump-probe Technique. , 2014, , .		0
103	Texture and morphology variations in $(\text{In,Ga})_2\text{Se}_3$ and $\text{Cu}(\text{In,Ga})\text{Se}_2$ thin films grown with various Se source conditions. Progress in Photovoltaics: Research and Applications, 2013, 21, 544-553.	4.4	36
104	Impact of a binary $\text{Ga}_2\text{Se}_3$ precursor on ternary $\text{CuGaSe}_2$ thin-film and solar cell device properties. Applied Physics Letters, 2013, 103, .	1.5	24
105	Local instability of $p$ -type bonding makes amorphous GeTe a lone-pair semiconductor. Physical Review B, 2013, 87, .	1.1	35
106	Vacancy-mediated three-center four-electron bonds in $\text{GeTe-Sb}_x\text{Te}_{1-x}$ phase-change memory alloys. Physical Review B, 2013, 87, .	1.1	76
107	Nanometer Resolution XANES Imaging of in situ switched individual PC-RAM devices. Materials Research Society Symposia Proceedings, 2013, 1563, 1.	0.1	1
108	Selective detection of tetrahedral units in amorphous GeTe-based phase change alloys using Ge L3-edge x-ray absorption near-edge structure spectroscopy. Applied Physics Letters, 2013, 102, 111904.	1.5	28

#	ARTICLE	IF	CITATIONS
109	Ultrafast optical manipulation of atomic motion in multilayer Ge-Sb-Te phase change materials. EPJ Web of Conferences, 2013, 41, 03007.	0.1	2
110	A hard X-ray nanospectroscopy station at SPring-8 BL39XU. Journal of Physics: Conference Series, 2013, 430, 012017.	0.3	25
111	Nanometer Resolution XANES Imaging of Individual PC-RAM Devices. Materials Research Society Symposia Proceedings, 2012, 1431, 26.	0.1	0
112	Polarization dependent optical control of atomic arrangement in multilayer Ge-Sb-Te phase change materials. Applied Physics Letters, 2012, 101, 232101.	1.5	15
113	Enhanced crystallization of GeTe from an Sb <sub>2</sub> Te <sub>3</sub> template. Applied Physics Letters, 2012, 100, .	1.5	56
114	Local structure of nitrogen in N-doped amorphous and crystalline GeTe. Applied Physics Letters, 2012, 100, .	1.5	25
115	Recrystallization of an amorphized epitaxial phase-change alloy: A phoenix arising from the ashes. Applied Physics Letters, 2012, 101, 061903.	1.5	18
116	Publisher's Note: Crystalline GeTe-based phase-change alloys: Disorder in order [Phys. Rev. B 86 (2012), 045212 (2012)]. Physical Review B, 2012, 86, .	1.1	0
117	A reconsideration of the thermodynamics of phase-change switching. Physica Status Solidi (B): Basic Research, 2012, 249, 1932-1938.	0.7	15
118	Epitaxial phase-change materials. Physica Status Solidi - Rapid Research Letters, 2012, 6, 415-417.	1.2	29
119	p-type conductivity of GeTe: The role of lone-pair electrons. Physica Status Solidi (B): Basic Research, 2012, 249, 1902-1906.	0.7	14
120	Disorder in order: A study of local and global order in Ge <sub>1-x</sub> Sb <sub>x</sub> Te alloys. Physica Status Solidi (B): Basic Research, 2012, 249, 1919-1924.	0.7	5
121	Crystalline GeTe-based phase-change alloys: Disorder in order. Physical Review B, 2012, 86, .	1.1	28
122	Athermal component of amorphisation in phase-change alloys and chalcogenide glasses. Journal of Non-Crystalline Solids, 2012, 358, 2398-2401.	1.5	7
123	Amorphous phase of GeTe-based phase-change memory alloys: Polyvalency of Ge <sub>1-x</sub> Te bonding and polymorphism. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1031-1035.	0.8	5
124	Comment on "New Structural Picture of the $Ge_2Sb_2$ Alloy". Physical Review Letters, 2012, 108, 239603; author reply 239602.	3.9	6
125	Bond-Selective Excitation and Following Displacement of Ge Atoms in GeTe/Sb <sub>2</sub> Te <sub>3</sub> Superlattice. Acta Physica Polonica A, 2012, 121, 336-339.	0.2	1
126	Characterization of CIGS thin films and solar cells grown with a plasma-cracked Se source. , 2011, , .		0



#	ARTICLE	IF	CITATIONS
127	Interfacial phase-change memory. Nature Nanotechnology, 2011, 6, 501-505.	15.6	630
128	Distortion-triggered loss of long-range order in solids with bonding energy hierarchy. Nature Chemistry, 2011, 3, 311-316.	6.6	178
129	CIGS thin films, solar cells, and submodules fabricated using a rf-plasma cracked Se-radical beam source. Thin Solid Films, 2011, 519, 7216-7220.	0.8	15
130	The order-disorder transition in GeTe: Views from different length-scales. Applied Physics Letters, 2011, 99, .	1.5	63
131	Effect of doping on global and local order in crystalline GeTe. Applied Physics Letters, 2011, 98, .	1.5	20
132	Local atomic order of crystalline Ge $\text{Sb}_8$ $\text{Sb}_2\text{Te}$ $\text{Sb}_2\text{Te}$	1.1	18
133	Electrical-field induced giant magnetoresistivity in (non-magnetic) phase change films. Applied Physics Letters, 2011, 99, 152105.	1.5	74
134	Intrinsic complexity of the melt-quenched amorphous Ge $\text{Sb}_2\text{Te}$ $\text{Sb}_2\text{Te}$ $\text{Sb}_2\text{Te}$	1.1	109
135	Pressure-induced structural transitions in phase-change materials based on Ge-free Sb-Te alloys. Physical Review B, 2011, 83, .	1.1	13
136	Optically Induced Sub-Wavelength Transient Apertures in Sb-Te Based Films. Materials Research Society Symposia Proceedings, 2011, 1338, 32001.	0.1	1
137	Development of high-efficiency flexible Cu(In,Ga)Se <sub>2</sub> solar cells: A study of alkali doping effects on CIS, CIGS, and CGS using alkali-silicate glass thin layers. Current Applied Physics, 2010, 10, S154-S156.	1.1	53
138	The role of vacancies in the pressure amorphisation phenomenon observed in Ge-Sb-Te phase change alloys. Materials Research Society Symposia Proceedings, 2010, 1251, 10.	0.1	0
139	Stress Limited Scaling of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> . Materials Research Society Symposia Proceedings, 2010, 1251, 2.	0.1	3
140	Amorphous InSb: Longer bonds yet higher density. Journal of Applied Physics, 2010, 108, 023506.	1.1	13
141	Non-melting super-resolution near-field apertures in Sb-Te alloys. Applied Physics Letters, 2010, 97, 161906.	1.5	33
142	The first principle computer simulation and real device characteristics of superlattice phase-change memory. , 2010, , .		2
143	Photoassisted amorphization of the phase-change memory alloy Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> Physical Review B, 2010, 82, .	1.1	80
144	Toward the Ultimate Limit of Phase Change in Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> . Nano Letters, 2010, 10, 414-419.	4.5	226

#	ARTICLE	IF	CITATIONS
145	Phase transition in crystalline GeTe: Pitfalls of averaging effects. Physical Review B, 2010, 82, .	1.1	95
146	Epitaxy of GeSbTe phase-change memory alloys. Applied Physics Letters, 2009, 94, .	1.5	32
147	Flexible Cu(In,Ga)Se <sub>2</sub> solar cells fabricated using alkali-silicate glass thin layers as an alkali source material. Journal of Renewable and Sustainable Energy, 2009, 1, 013102.	0.8	38
148	Epitaxial Phase Change Materials: Growth and Switching of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> on GaSb(001). Materials Research Society Symposia Proceedings, 2009, 1160, 1.	0.1	3
149	Liquid Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> studied by extended x-ray absorption. Applied Physics Letters, 2009, 95, .	1.5	27
150	Crystallization of Bi Doped Sb <sub>8</sub> Te <sub>2</sub> . Japanese Journal of Applied Physics, 2009, 48, 03A062.	0.8	5
151	What is the Origin of Activation Energy in Phase-Change Film?. Japanese Journal of Applied Physics, 2009, 48, 03A053.	0.8	48
152	Local structure of amorphous Ge <sub>1-x</sub> Sb <sub>x</sub> Te alloys: Ge umbrella flip <i>vs</i> . DFT simulations. Physica Status Solidi (B): Basic Research, 2009, 246, 1826-1830.	0.7	12
153	Large grain Cu(In,Ga)Se <sub>2</sub> thin film growth using a Se-radical beam source. Solar Energy Materials and Solar Cells, 2009, 93, 792-796.	3.0	24
154	Thermal conductivity of low-k films of varying porosity and direct measurements on silicon substrate. Microelectronic Engineering, 2009, 86, 1009-1012.	1.1	5
155	Band profiles of ZnMgO/ZnO heterostructures confirmed by Kelvin probe force microscopy. Applied Physics Letters, 2009, 94, .	1.5	32
156	A Sensitive Multilayered Structure Suitable for Biosensing on the BioDVD Platform. Analytical Chemistry, 2009, 81, 4963-4970.	3.2	47
157	Initial Structure Memory of Pressure-Induced Changes in the Phase-Change Memory Alloy $Ge_2Sb_2Te_5$ . Physical Review Letters, 2009, 103, 115502.	2.9	51
158	Na-induced variations in the structural, optical, and electrical properties of Cu(In,Ga)Se <sub>2</sub> thin films. Journal of Applied Physics, 2009, 106, .	1.1	148
159	Proposal of a grating-based optical reflection switch using phase change materials. Optics Express, 2009, 17, 16947.	1.7	13
160	Short and Long-Range Order in Phase Change Materials. , 2009, , 149-174.		2
161	Thermal conductivity measurements of low-k films using thermoreflectance phenomenon. Microelectronic Engineering, 2008, 85, 796-799.	1.1	11
162	Alkali incorporation control in Cu(In,Ga)Se <sub>2</sub> thin films using silicate thin layers and applications in enhancing flexible solar cell efficiency. Applied Physics Letters, 2008, 93, .	1.5	71

#	ARTICLE	IF	CITATIONS
163	Polarization-induced two-dimensional electron gases in ZnMgO/ZnO heterostructures. Applied Physics Letters, 2008, 93, .	1.5	131
164	Role of Ge Switch in Phase Transition: Approach using Atomically Controlled GeTe/Sb <sub>2</sub> Te <sub>3</sub> Superlattice. Japanese Journal of Applied Physics, 2008, 47, 5763.	0.8	68
165	Large Optical Transitions in Rewritable Digital Versatile Discs: An Interlayer Atomic Zipper in a SbTe Alloy. Materials Research Society Symposia Proceedings, 2008, 1072, 1.	0.1	0
166	Changes in Electronic Structure and Chemical Bonding upon Crystallization of the Phase Change Material $\text{GeSb}_2\text{Te}_5$ . Physical Review Letters, 2008, 100, 016402.	2.9	65
167	Temperature independence of pressure-induced amorphization of the phase-change memory alloy Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> . Applied Physics Letters, 2008, 93, .	1.5	32
168	Reduction in crystallization time of Sb:Te films through addition of Bi. Applied Physics Letters, 2008, 92, .	1.5	23
169	Structure in the local environment of Zn <sup>2+</sup> ion in the anti-termination protein of Bacillus subtilis. Acta Crystallographica Section A: Foundations and Advances, 2008, 64, C110-C111.	0.3	0
170	X-Ray Fluorescence Holographic Study on a Single-Crystal Thin Film of a Rewritable Optical Media. AIP Conference Proceedings, 2007, . .	0.3	0
171	Sub-Nanosecond Time-Resolved Structural Measurements of the Phase-Change Alloy Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> . Japanese Journal of Applied Physics, 2007, 46, 3711-3714.	0.8	13
172	A Reversible Change of Reflected Light Intensity between Molten and Solidified Ge-Sb-Te Alloy. Japanese Journal of Applied Physics, 2007, 46, L868-L870.	0.8	10
173	Thermal Conductivity Measurements of Sb-Te Alloy Thin Films Using a Nanosecond Thermoreflectance Measurement System. Japanese Journal of Applied Physics, 2007, 46, 6863-6864.	0.8	20
174	Temperature Dependence of the Thermal Properties of Optical Memory Materials. Japanese Journal of Applied Physics, 2007, 46, 3909-3911.	0.8	39
175	A possible mechanism of ultrafast amorphization in phase-change memory alloys: an ion slingshot from the crystalline to amorphous position. Journal of Physics Condensed Matter, 2007, 19, 455209.	0.7	20
176	Formation of two-dimensional electron gas and enhancement of electron mobility by Zn polar ZnMgO/ZnO heterostructures. , 2007, 6474, 78.		0
177	Pressure-induced amorphization of quasibinary GeTe-Sb <sub>2</sub> Te <sub>3</sub> : The role of vacancies. Applied Physics Letters, 2007, 91, 021911.	1.5	35
178	Existence of tetrahedral site symmetry about Ge atoms in a single-crystal film of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> found by x-ray fluorescence holography. Applied Physics Letters, 2007, 90, 131913.	1.5	31
179	Preparation of Cu(In <sub>1-x</sub> Ga <sub>x</sub> )Se <sub>2</sub> Thin Films and Solar Cells Using a Se-radical Beam Source. Materials Research Society Symposia Proceedings, 2007, 1012, 1.	0.1	2
180	Growth of polycrystalline Cu(In,Ga)Se <sub>2</sub> thin films using a radio frequency-cracked Se-radical beam source and application for photovoltaic devices. Applied Physics Letters, 2007, 91, .	1.5	29

#	ARTICLE	IF	CITATIONS
181	Strong excitonic transition of Zn <sub>1-x</sub> Mg <sub>x</sub> O alloy. Applied Physics Letters, 2007, 91, .	1.5	55
182	Direct Observation of Nitrogen Location in Molecular Beam Epitaxy Grown Nitrogen-Doped ZnO. AIP Conference Proceedings, 2007, . .	0.3	2
183	Phase-change optical recording: Past, present, future. Thin Solid Films, 2007, 515, 7534-7537.	0.8	23
184	Measurement of the thermal conductivity of nanometer scale thin films by thermoreflectance phenomenon. Microelectronic Engineering, 2007, 84, 1792-1796.	1.1	40
185	Raman scattering study of GeTe and Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> phase-change materials. Journal of Physics and Chemistry of Solids, 2007, 68, 1074-1078.	1.9	164
186	High electron mobility Zn polar ZnMgO/ZnO heterostructures grown by molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 358-361.	0.7	33
187	Why DVDs work the way they do: The nanometer-scale mechanism of phase change in Ge <sub>1-x</sub> Sb <sub>x</sub> Te alloys. Journal of Non-Crystalline Solids, 2006, 352, 1612-1615.	1.5	28
188	Control of the thin film properties of Cu(In,Ga)Se <sub>2</sub> using water vapor introduction during growth. Journal of Applied Physics, 2006, 100, 096106.	1.1	11
189	Determination of crystallographic polarity of ZnO bulk crystals and epilayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1018-1021.	0.8	5
190	Photoluminescence recombination centers in ZnO. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1026-1029.	0.8	0
191	Nanometer-scale mechanism of phase-change optical recording as revealed by XAFS. Nuclear Instruments & Methods in Physics Research B, 2006, 246, 69-74.	0.6	1
192	Soft X-ray XANES of N in ZnO:N " Why is doping so difficult?. Nuclear Instruments & Methods in Physics Research B, 2006, 246, 75-78.	0.6	15
193	Structural changes of CIGS during deposition investigated by spectroscopic light scattering: A study on Ga concentration and Se pressure. Solar Energy Materials and Solar Cells, 2006, 90, 3377-3384.	3.0	6
194	Localized Light Focusing and Super Resolution Readout via Chalcogenide Thin Film. Materials Research Society Symposia Proceedings, 2006, 918, 1.	0.1	3
195	Two-dimensional electron gas in Zn polar ZnMgO <sub>1-x</sub> ZnO heterostructures grown by radical source molecular beam epitaxy. Applied Physics Letters, 2006, 89, 132113.	1.5	118
196	X-ray absorption spectroscopy of high-k gate dielectric insulating layers for next-generation semiconductor devices as measured by superconducting detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2006, 559, 731-733.	0.7	1
197	Characteristics of nanostructured Ag films by the reduction of sputtered AgO <sub>x</sub> thin films. Nanotechnology, 2006, 17, 79-82.	1.3	15
198	Read-out enhancement of super-resolution near-field structures using the pit shape. Nanotechnology, 2006, 17, 1481-1483.	1.3	5

#	ARTICLE	IF	CITATIONS
199	Measurements of Temperature Dependence of Optical and Thermal Properties of Optical Disk Materials. Japanese Journal of Applied Physics, 2006, 45, 1419-1421.	0.8	43
200	What Makes Phase-Change Chalcogenide Alloys Materials of Choice for Optical Data Storage. Materials Research Society Symposia Proceedings, 2006, 918, 5.	0.1	1
201	Understanding Structural Changes in Phase Change Memory Alloys. Materials Research Society Symposia Proceedings, 2006, 918, 1.	0.1	2
202	Pressure-Induced Site-Selective Disorder of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> : A New Insight into Phase-Change Optical Recording. Physical Review Letters, 2006, 97, 035701.	2.9	100
203	Direct Observation of Nitrogen Location in Molecular Beam Epitaxy Grown Nitrogen-Doped ZnO. Physical Review Letters, 2006, 96, 045504.	2.9	119
204	On a thermally induced readout mechanism in super-resolution optical disks. Journal of Applied Physics, 2006, 100, 043106.	1.1	37
205	XAFS Observations of Initial Growth of 0001 ZnO on Sapphire Substrates. Physica Scripta, 2005, , 523.	1.2	0
206	High-pressure induced structural changes in metastable Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films: An X-ray absorption study. Nuclear Instruments & Methods in Physics Research B, 2005, 238, 160-162.	0.6	7
207	The effects of thermal treatments on the electrical properties of phosphorus doped ZnO layers grown by MBE. Journal of Crystal Growth, 2005, 278, 268-272.	0.7	33
208	Improvement in the aspect ratio of fabricated minute dots by the volume change thermal lithography technique. Microelectronic Engineering, 2005, 78-79, 359-363.	1.1	3
209	Improvement of ZnO TCO film growth for photovoltaic devices by reactive plasma deposition (RPD). Thin Solid Films, 2005, 480-481, 199-203.	0.8	57
210	Structural changes of CuGaSe <sub>2</sub> films during the three-stage process observed by spectroscopic light scattering. Thin Solid Films, 2005, 480-481, 367-372.	0.8	2
211	Fabrication of wide-gap Cu(In <sub>1-x</sub> Ga <sub>x</sub> )Se <sub>2</sub> thin film solar cells: a study on the correlation of cell performance with highly resistive i-ZnO layer thickness. Solar Energy Materials and Solar Cells, 2005, 87, 541-548.	3.0	108
212	Growth of ZnO and device applications. Applied Surface Science, 2005, 244, 504-510.	3.1	32
213	An XAFS Study of Amorphous Crystalline Phase Transitions along the GeTe-Sb <sub>2</sub> Te <sub>3</sub> Pseudobinary Tie Line. , 2005, , WC4.		0
214	Development of a geometrical evaluation apparatus for ultrahigh 100 GB optical disk masters. Review of Scientific Instruments, 2005, 76, 083706.	0.6	3
215	Photoluminescence characterization of excitonic centers in ZnO epitaxial films. Applied Physics Letters, 2005, 86, 221907.	1.5	22
216	Why Phase-Change Media Are Fast and Stable: A New Approach to an Old Problem. Japanese Journal of Applied Physics, 2005, 44, 3345-3349.	0.8	55

#	ARTICLE	IF	CITATIONS
217	Determination of crystallographic polarity of ZnO layers. Applied Physics Letters, 2005, 87, 141904.	1.5	63
218	Degenerate layers in epitaxial ZnO films grown on sapphire substrates. Applied Physics Letters, 2004, 84, 4412-4414.	1.5	65
219	Improved External Efficiency InGaN-Based Light-Emitting Diodes with Transparent Conductive Ga-Doped ZnO as p-Electrodes. Japanese Journal of Applied Physics, 2004, 43, L180-L182.	0.8	59
220	Understanding the phase-change mechanism of rewritable optical media. Nature Materials, 2004, 3, 703-708.	13.3	1,193
221	Doping properties of ZnO thin films for photovoltaic devices grown by URT-IP (ion plating) method. Thin Solid Films, 2004, 451-452, 219-223.	0.8	25
222	InGaN-based light-emitting diodes fabricated with transparent Ga-doped ZnO as ohmicp-contact. Physica Status Solidi A, 2004, 201, 2704-2707.	1.7	13
223	In situ diagnostic methods for thin-film fabrication: utilization of heat radiation and light scattering. Progress in Photovoltaics: Research and Applications, 2004, 12, 219-234.	4.4	57
224	Thermal processing induced structural changes in ZnO films grown on (11 $\bar{2}$ 0) sapphire substrates using molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 868-871.	0.8	0
225	Characterization of ZnO crystals by photoluminescence spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 872-875.	0.8	22
226	Effects of low temperature buffer layer treatments on the growth of high quality ZnO films. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 888-891.	0.8	9
227	An option for the surface science on Cu chalcopyrites: the selenium capping and decapping process. Surface Science, 2004, 557, 263-268.	0.8	21
228	Crystallization-induced short-range order changes in amorphous GeTe. Journal of Physics Condensed Matter, 2004, 16, S5103-S5108.	0.7	58
229	Effect of band offset on the open circuit voltage of heterojunction CuIn $_{1-x}$ Ga $_x$ Se $_2$ solar cells. Applied Physics Letters, 2004, 85, 5607-5609.	1.5	38
230	Band-gap modified Al-doped Zn $_{1-x}$ Mg $_x$ O transparent conducting films deposited by pulsed laser deposition. Applied Physics Letters, 2004, 85, 1374-1376.	1.5	131
231	An EXAFS and XANES study of MBE grown Cu-doped ZnO. Nuclear Instruments & Methods in Physics Research B, 2003, 199, 190-194.	0.6	25
232	Properties of CuInGaSe $_2$ solar cells based upon an improved three-stage process. Thin Solid Films, 2003, 431-432, 6-10.	0.8	30
233	In situ deposition rate monitoring during the three-stage-growth process of Cu(In,Ga)Se $_2$ absorber films. Thin Solid Films, 2003, 431-432, 16-21.	0.8	18
234	ZnO transparent conducting films deposited by pulsed laser deposition for solar cell applications. Thin Solid Films, 2003, 431-432, 369-372.	0.8	237

#	ARTICLE	IF	CITATIONS
235	Electron beam probe quantization of compound composition: surface phases and surface roughness. <i>Thin Solid Films</i> , 2003, 431-432, 277-283.	0.8	12
236	Natural ordering of ZnO $_{1-x}$ Se $_x$ grown by radical source MBE. <i>Journal of Crystal Growth</i> , 2003, 251, 633-637.	0.7	5
237	The chemical environment about Cd atoms in Cd chemical bath treated CuInSe $_2$ and CuGaSe $_2$ . <i>Journal of Physics and Chemistry of Solids</i> , 2003, 64, 1733-1735.	1.9	5
238	Adjusting the sodium diffusion into CuInGaSe $_2$ absorbers by preheating of Mo/SLG substrates. <i>Journal of Physics and Chemistry of Solids</i> , 2003, 64, 1877-1880.	1.9	12
239	Growth and electrical properties of ZnO thin films deposited by novel ion plating method. <i>Thin Solid Films</i> , 2003, 445, 274-277.	0.8	51
240	Local structure of crystallized GeTe films. <i>Applied Physics Letters</i> , 2003, 82, 382-384.	1.5	114
241	Cu(In $_{1-x}$ Ga $_x$ )Se $_2$ growth studies by in situ spectroscopic light scattering. <i>Applied Physics Letters</i> , 2003, 82, 2091-2093.	1.5	43
242	Estimation and Correction Procedure for the Effects of Surface Roughness on Electron Probe Microanalysis. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 5811-5812.	0.8	1
243	Local Structure of AgO $_x$ Thin Layers Generating Optical Near Field: an X-Ray Absorption Fine Structure Study. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 1022-1025.	0.8	6
244	High-Quality Transparent Conducting Oxide Films Deposited by a Novel Ion Plating Technique. <i>Materials Research Society Symposia Proceedings</i> , 2003, 763, 741.	0.1	4
245	Point Defect Changes in CuGaSe $_2$ Induced by Gas Annealing. <i>Materials Research Society Symposia Proceedings</i> , 2003, 763, 5171.	0.1	3
246	Bandgap Engineering of ZnO Transparent Conducting Films. <i>Materials Research Society Symposia Proceedings</i> , 2003, 763, 721.	0.1	4
247	Observation of Exciton-Polariton Emissions from a ZnO Epitaxial Film on the a-Face of Sapphire Grown by Radical-Source Molecular-Beam-Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2002, 41, L935-L937.	0.8	19
248	A XANES Study of Cu Valency in Cu-Doped Epitaxial ZnO. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 849-852.	0.7	19
249	Bandgap Engineering of ZnO Using Se. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 887-890.	0.7	32
250	Photoreflectance and Photoluminescence of Exciton-Polaritons in a ZnO Epilayer Grown on the a-Face of Sapphire by Radical-Source Molecular-Beam Epitaxy. <i>Physica Status Solidi A</i> , 2002, 192, 171-176.	1.7	7
251	Room-temperature deposition of Al-doped ZnO films by oxygen radical-assisted pulsed laser deposition. <i>Thin Solid Films</i> , 2002, 422, 176-179.	0.8	52
252	Growth of N-doped and Ga+N-codoped ZnO films by radical source molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2002, 237-239, 503-508.	0.7	54

#	ARTICLE	IF	CITATIONS
253	Molecular beam epitaxial growth and characterization of CuInSe <sub>2</sub> and CuGaSe <sub>2</sub> for device applications. Journal of Crystal Growth, 2002, 237-239, 1993-1999.	0.7	23
254	Static analysis of off-axis crystal film growth onto a lattice-mismatched substrate. Applied Physics Letters, 2001, 79, 608-610.	1.5	17
255	Growth of Undoped ZnO Films with Improved Electrical Properties by Radical Source Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2001, 40, 250-254.	0.8	85
256	Control of Optical and Electrical Properties of ZnO Films for Photovoltaic Applications. Materials Research Society Symposia Proceedings, 2001, 668, 1.	0.1	3
257	Significant Compositional Changes and Formation of a Ga-O Phase after Oxygen-annealing of Ga-rich CuGaSe <sub>2</sub> Films. Materials Research Society Symposia Proceedings, 2001, 668, 1.	0.1	2
258	Observation of Interdiffusion in ZnO/CuInSe <sub>2</sub> Heterostructures and its Effect on Film Properties. Materials Research Society Symposia Proceedings, 2001, 668, 1.	0.1	4
259	Anion vacancies in CuInSe <sub>2</sub> . Thin Solid Films, 2001, 387, 129-134.	0.8	30
260	Optical properties of high-quality CuGaSe <sub>2</sub> epitaxial layers examined by piezoelectric photoacoustic spectroscopy. Solar Energy Materials and Solar Cells, 2001, 67, 173-178.	3.0	2
261	Nucleation and growth of ZnO on sapphire substrates using molecular beam epitaxy. Journal of Crystal Growth, 2001, 227-228, 911-916.	0.7	21
262	Growth and characterization of undoped ZnO films for single crystal based device use by radical source molecular beam epitaxy (RS-MBE). Journal of Crystal Growth, 2001, 227-228, 923-928.	0.7	35
263	Photoluminescence properties of sodium incorporation in CuInSe <sub>2</sub> and CuIn <sub>3</sub> Se <sub>5</sub> thin films. Solar Energy Materials and Solar Cells, 2001, 67, 289-295.	3.0	24
264	Far-infrared optical conductivity of YBCO single crystal thin films from transmission and reflection spectra. Journal of Physics and Chemistry of Solids, 2001, 62, 253-256.	1.9	2
265	Local structure of Ge nanoislands on Si(111) surfaces with a SiO <sub>2</sub> coverage. Applied Physics Letters, 2001, 78, 2563-2565.	1.5	47
266	Interactions between gallium and nitrogen dopants in ZnO films grown by radical-source molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 4139-4141.	1.5	132
267	Improvement of Electrical Properties in ZnO Thin Films Grown by Radical Source(RS)-MBE. Physica Status Solidi A, 2000, 180, 287-292.	1.7	41
268	ZnO growth on Si by radical source MBE. Journal of Crystal Growth, 2000, 214-215, 50-54.	0.7	116
269	Nitrogen-induced defects in ZnO:N grown on sapphire substrate by gas source MBE. Journal of Crystal Growth, 2000, 209, 526-531.	0.7	152
270	Uniaxial locked growth of high-quality epitaxial ZnO films on -Al <sub>2</sub> O <sub>3</sub> . Journal of Crystal Growth, 2000, 209, 532-536.	0.7	85



#	ARTICLE	IF	CITATIONS
271	Far-infrared optical conductivity of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> thin films. Physica C: Superconductivity and Its Applications, 2000, 341-348, 2197-2200.	0.6	0
272	Temperature variation of nonradiative carrier recombination processes in high-quality CuGaSe <sub>2</sub> thin films grown by molecular beam epitaxy. Applied Physics Letters, 2000, 77, 259-261.	1.5	11
273	Uniaxial locked epitaxy of ZnO on the a face of sapphire. Applied Physics Letters, 2000, 77, 1801.	1.5	192
274	Control of Intrinsic Defects in CuInSe <sub>2</sub> Films for Device Applications. Japanese Journal of Applied Physics, 2000, 39, 149.	0.8	3
275	A High Resolution X-ray Diffraction and TEM Study of the Cu <sub>x</sub> Se Surface Phase of Cu-rich CuInSe <sub>2</sub> . Japanese Journal of Applied Physics, 2000, 39, 189.	0.8	2
276	Twin formation in Cu-Ga-Se films grown by molecular beam epitaxy under Ga-excess conditions. Japanese Journal of Applied Physics, 2000, 39, 200.	0.8	3
277	Exciton structures of single- and polycrystalline CuInSe <sub>2</sub> and CuGaSe <sub>2</sub> . Japanese Journal of Applied Physics, 2000, 39, 326.	0.8	0
278	Disappearance of the surface Cu-Se second phase during post-growth annealing of CuInSe <sub>2</sub> epitaxial films grown under excess Cu-flux conditions. Japanese Journal of Applied Physics, 2000, 39, 205.	0.8	1
279	Effects of Sodium on CuIn <sub>3</sub> Se <sub>5</sub> Thin Films. Japanese Journal of Applied Physics, 1999, 38, L899-L901.	0.8	12
280	Electron Probe Microanalysis of Second Phases via Acceleration Voltage Dependence. Japanese Journal of Applied Physics, 1999, 38, L96-L98.	0.8	6
281	Deposition of Ge <sub>1-x</sub> C <sub>x</sub> Alloy on Si by Combined Low-Energy Ion Beam and Molecular Beam Epitaxial Method. Japanese Journal of Applied Physics, 1999, 38, 3459-3465.	0.8	6
282	Optical characterizations of CuInSe <sub>2</sub> epitaxial layers grown by molecular beam epitaxy. Journal of Applied Physics, 1999, 86, 4354-4359.	1.1	23
283	Effects of the surface Cu <sub>2-x</sub> Se phase on the growth and properties of CuInSe <sub>2</sub> films. Applied Physics Letters, 1999, 74, 1630-1632.	1.5	66
284	Epitaxial growth of ZnO thin films on LiNbO <sub>3</sub> substrates. Thin Solid Films, 1999, 347, 238-240.	0.8	40
285	Growth of high-quality epitaxial ZnO films on $\alpha$ -Al <sub>2</sub> O <sub>3</sub> . Journal of Crystal Growth, 1999, 201-202, 627-632.	0.7	173
286	Control of intrinsic defects in molecular beam epitaxy grown CuInSe <sub>2</sub> . Journal of Crystal Growth, 1999, 201-202, 1061-1064.	0.7	9
287	Growth of LiNbO <sub>3</sub> epitaxial films by oxygen radical-assisted laser molecular beam epitaxy. Applied Physics A: Materials Science and Processing, 1999, 69, S679-S681.	1.1	15
288	Piezoelectric photoacoustic spectra of CuInSe <sub>2</sub> thin film grown by molecular beam epitaxy. Thin Solid Films, 1999, 343-344, 591-593.	0.8	3

#	ARTICLE	IF	CITATIONS
289	Temperature dependence of photoacoustic spectra in CuInSe <sub>2</sub> thin films grown by molecular beam epitaxy. Solar Energy Materials and Solar Cells, 1998, 50, 127-132.	3.0	12
290	Formalistic description of multislice calculation method. , 1998, 40, 152-161.		0
291	Direct observation of the Cu <sub>2</sub> ~ <sup>x</sup> Se phase of Cu-rich epitaxial CuInSe <sub>2</sub> grown on GaAs (001). Journal of Applied Physics, 1998, 84, 6926-6928.	1.1	23
292	Band gap energies of bulk, thin-film, and epitaxial layers of CuInSe <sub>2</sub> and CuGaSe <sub>2</sub> . Journal of Applied Physics, 1998, 83, 3678-3689.	1.1	115
293	Effect of strain and temperature on anomalously large interdiffusion in InAsP/InP heterostructures. Applied Physics Letters, 1997, 70, 3410-3412.	1.5	4
294	Piezoelectric Photoacoustic Spectra In CuGaSe <sub>2</sub> Thin Films Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1997, 485, 151.	0.1	0
295	In-Situ Surface Composition Measurements of CuGaSe <sub>2</sub> Thin Films. Materials Research Society Symposia Proceedings, 1997, 485, 145.	0.1	0
296	A shallow state in molecular beam epitaxial grown CuGaSe <sub>2</sub> film detectable by 1.62 eV photoluminescence. Journal of Applied Physics, 1997, 81, 2794-2798.	1.1	36
297	Second-harmonic generation from CuInSe <sub>2</sub> /thin films: influence of the substrate-epilayer lattice mismatch. IEEE Journal of Quantum Electronics, 1997, 33, 1294-1298.	1.0	11
298	Effects of strain on the growth and properties of CuInSe <sub>2</sub> epitaxial films. Journal of Crystal Growth, 1997, 175-176, 1051-1056.	0.7	4
299	Effects of annealing on CuInSe <sub>2</sub> films grown by molecular beam epitaxy. Solar Energy Materials and Solar Cells, 1997, 49, 319-326.	3.0	15
300	Observation of diamond crystallites in thin films prepared by laser ablation of hard fullerene-based carbon. Journal Physics D: Applied Physics, 1996, 29, 929-933.	1.3	13
301	The Effects of Kcn Etching on Cu-Rich Epitaxial CuInSe <sub>2</sub> Thin Films. Materials Research Society Symposia Proceedings, 1996, 426, 213.	0.1	3
302	Growth of Ge <sub>1-x</sub> C <sub>x</sub> Alloys on Si by Combined Low-Energy Ion Beam and Molecular Beam Epitaxy Method. Materials Research Society Symposia Proceedings, 1996, 438, 393.	0.1	1
303	Growth of Ge <sub>1</sub> ~ <sup>x</sup> C <sub>x</sub> , Alloys on Si by Combined Low-Energy Ion Beam and Molecular Beam Epitaxy Method. Materials Research Society Symposia Proceedings, 1996, 439, 233.	0.1	0
304	Structural and Surface Morphology Changes in CuInSe <sub>2</sub> Thin Films as a Function of Cu/In Ratio. Materials Research Society Symposia Proceedings, 1996, 441, 9.	0.1	0
305	The strain energy density of cubic epitaxial layers. Journal of Crystal Growth, 1996, 160, 406-412.	0.7	18
306	Growth of CuGaSe <sub>2</sub> film by molecular beam epitaxy. Microelectronics Journal, 1996, 27, 53-58.	1.1	21

#	ARTICLE	IF	CITATIONS
307	Band-edge photoluminescence of CuGaSe <sub>2</sub> films grown by molecular beam epitaxy. Journal of Applied Physics, 1996, 79, 4318.	1.1	36
308	Evidence of crystalline diamond in thin films prepared by laser ablation of hard fullerene-based carbon. Journal of Applied Physics, 1996, 80, 1182-1185.	1.1	6
309	Determination of the composition of strained tetragonal epilayers. Applied Physics Letters, 1996, 69, 761-763.	1.5	2
310	High quality CuInSe <sub>2</sub> films grown on pseudo-lattice-matched substrates by molecular beam epitaxy. Applied Physics Letters, 1996, 69, 647-649.	1.5	48
311	Cation sublattice stacking faults in Cu-rich chalcopyrite CuInSe <sub>2</sub> . Journal of Materials Research, 1996, 11, 1398-1402.	1.2	2
312	Translational Phase Domains in the Cation Sublattice of Chalcopyrite Compounds. Japanese Journal of Applied Physics, 1996, 35, L843-L845.	0.8	3
313	Defect Structure of Cu-Rich and In-Rich Chalcopyrite CuInSe <sub>2</sub> Films Grown on GaAs. Materials Research Society Symposia Proceedings, 1995, 399, 467.	0.1	0
314	Strain-Induced Diffusion in Heteroepitaxially Grown CuInSe <sub>2</sub> on GaAs Substrates. Materials Research Society Symposia Proceedings, 1995, 399, 549.	0.1	3
315	Determination of the lattice constants of epitaxial layers. Journal of Crystal Growth, 1995, 154, 401-409.	0.7	12
316	Heteroepitaxy and characterization of CuInSe <sub>2</sub> on GaAs(001). Journal of Crystal Growth, 1995, 150, 1201-1205.	0.7	64
317	The Strain Energy Densities of Hexagonal and Tetragonal Epitaxial Media. Japanese Journal of Applied Physics, 1995, 34, L1616-L1619.	0.8	5
318	Excitonic emissions from CuInSe <sub>2</sub> on GaAs(001) grown by molecular beam epitaxy. Applied Physics Letters, 1995, 67, 1289-1291.	1.5	53
319	Ion-beam doping of GaAs with low-energy (100 eV) C <sup>+</sup> using combined ion-beam and molecular-beam epitaxy. Journal of Applied Physics, 1995, 77, 146-152.	1.1	20
320	Photoluminescence investigation of Hg acceptor in GaAs. Applied Physics Letters, 1995, 67, 1465-1467.	1.5	3
321	Fermi surface dependence of the hall coefficient in quasi-2D molecular conductors. Synthetic Metals, 1995, 70, 1001-1004.	2.1	4
322	Vacuum ultraviolet photolysis of supersonic free jets of SiH <sub>4</sub> . Applied Surface Science, 1994, 79-80, 476-480.	3.1	6
323	Photoluminescence investigation of a new emission formed in Mn <sup>+</sup> implanted ultra-pure GaAs grown by MBE. , 1994, , 373-376.		0
324	Selective Dissociative Ionization of SiH <sub>4</sub> , Si <sub>2</sub> H <sub>6</sub> and Si <sub>3</sub> H <sub>8</sub> by Electron Impact in Supersonic Free Jets. Japanese Journal of Applied Physics, 1993, 32, L879-L882.	0.8	8

#	ARTICLE	IF	CITATIONS
325	Epitaxial growth of Si by ArF laser-excited supersonic free jets of Si <sub>2</sub> H <sub>6</sub> . Applied Physics Letters, 1993, 63, 3473-3475.	1.5	14
326	Low energy (100 eV) C <sup>+</sup> ion doping into GaAs using combined ion beam and molecular beam epitaxial technology. Applied Physics Letters, 1993, 63, 1951-1953.	1.5	16
327	Optical Characterization of 100 eV C <sup>+</sup> Ion Doped GaAs. Materials Research Society Symposia Proceedings, 1993, 300, 357.	0.1	2
328	Effects of Hyperthermal Carbon Subimplantation Doping on the Raman Spectra of GaAs. Materials Research Society Symposia Proceedings, 1993, 316, 1011.	0.1	1
329	Low temperature photoluminescence from GaAs impinged by mass-separated low-energy C <sup>+</sup> ion beams during molecular beam epitaxy. Materials Research Society Symposia Proceedings, 1993, 316, 1029.	0.1	5
330	Molecular dynamics and quasidynamics simulations of low-energy ion/surface interactions leading to decreased epitaxial temperatures and increased dopant incorporation probabilities during Si MBE. Journal of Crystal Growth, 1991, 111, 870-875.	0.7	10
331	Amorphization Processes in Ion Implanted Si: Temperature Dependence. Japanese Journal of Applied Physics, 1991, 30, 3617-3620.	0.8	9
332	Molecular dynamics and quasidynamics simulations of the annealing of bulk and near-surface interstitials formed in molecular beam epitaxial Si due to low-energy particle bombardment during deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 91-97.	0.9	51
333	Molecular dynamics simulations of low-energy particle bombardment effects during vapor-phase crystal growth: 10 eV Si atoms incident on Si(001)2 $\times$ 1 surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 3726-3735.	0.9	65
334	Molecular Dynamics Simulations of Low-Energy Ion/Surface Interactions During Vapor Phase Crystal Growth: 10 eV Si Incident on Si(001)2 $\times$ 1. Materials Research Society Symposia Proceedings, 1989, 157, 259.	0.1	7
335	Electrical properties of Si(100) films doped with low-energy (~150 eV) Sb ions during growth by molecular beam epitaxy. Applied Physics Letters, 1988, 53, 1732-1734.	1.5	34
336	Determination of the valence electronic structure of condensed trimethylaluminum by photoelectron spectroscopy and molecular-orbital calculations. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 3115-3119.	0.9	9
337	Electronic Structure of Adsorbed Trimethylaluminum on Clean Si(100) Surfaces. Materials Research Society Symposia Proceedings, 1988, 131, 345.	0.1	2
338	Natural ordering of ZnO/ <sub>x</sub> /Se/ <sub>x</sub> / grown by radical source MBE. , 0, , .		0
339	Local structure of AgO/ <sub>x</sub> / thin layers generating optical near-field. , 0, , .		0
340	Laser-induced Ge Atom Switching as a Key to Understanding Phase-change Optical Media. , 0, , .		0
341	In-situ Raman Scattering Spectroscopy for a Super Resolution Optical Disk during Readout. Applied Physics Express, 0, 2, 082402.	1.1	7